



HL-304PT1C-T



Features

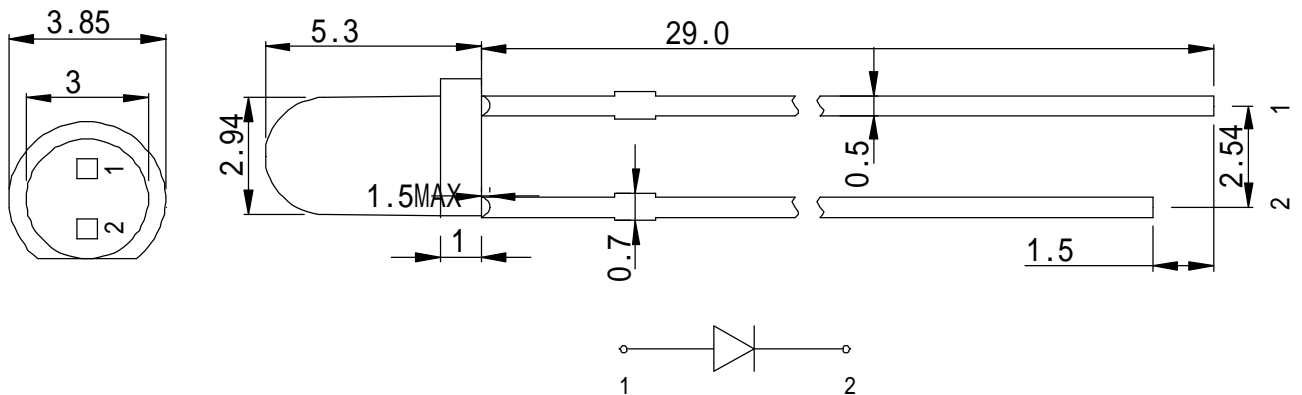
- Mechanically and spectrally matchend to the infrared emitting LED LAMP.
- Color Transparent Lens.
- Rohs compliant.

Package Dimensions

Description

Made with NPN silicon phototransistor chips.

- 1: ANODE
2: CATHODE



Tolerance Grade	Dimension Tolerance (UNIT:mm)			
	0.5~3	3~6	6~30	30~120
	±0.1	±0.2	±0.3	±0.5

Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
V _{BR CEO}	Collector-Emitter Breakdown Voltage	30	-	100	V	I _c =100uA E _e =0mW/cm ²
V _{BR ECO}	Emitter-to-Collector Breakdown Voltage	6.5	-	-	V	I _e =100uA E _e =0mW/cm ²
V _{CE (SAT)}	Collector-to-Emitter Saturation Voltage	-	-	0.2	V	I _c =100uA E _e =20mW/cm ²
I _{CEO}	Collector Dark Current	-	-	100	nA	V _{CE} =100uA E _e =0mW/cm ²
T _R	Rise Time (10% to 90%)	-	15	-	us	V _{CE} =5V I _C =1mA R _L =1000Ω
T _F	Fall Time (90% to 10%)	-	15	-	us	
I _(ON)	On State Collector Current	0.1	0.5	-	mA	V _{CE} =5V E _e =1mW/cm ² λ=940nm

Absolute Maximum ratings at Ta=25°C

Parameter	Max Ratings
Collector-to-Emitter Breakdown Voltage	30V
Emitter-to-Collector Breakdown Voltage	6.5V
Power Dissipation at (or below) 25°C Free Air Temperature	100mW
Operating Temperature Range	-30°C~80°C
Storage Temperature Range	-30°C~80°C
Lead Soldering Temperature (>3mm for 5sec)	260°C

Soldering:

1. Manual Of Soldering

The temperature of the iron tip should not be higher than 300°C and Soldering within 3 seconds per solder-land is to be observed.

2. DIP soldering (Wave Soldering):

Preheating: 120°C~150°C, within 120~180 sec.

Operation heating: 245°C ± 5°C within 5 sec. 260°C (Max)

Gradual Cooling (Avoid quenching).

